

Attorney's Docket No.: 07977/213002

REMARKS

Reconsideration and allowance of the above referenced application are respectfully requested.

The claims stand objected to based on various informalities. Claims 23, 39, 47, 63 and 71 have been amended to show proper dependency. Claims 48, 55, and 64 have been amended to obviate the rejections of "substantial duplication". Claims 9-12, 14-16 and 23 are indicate as being objectionable as being substantial duplicates of claims 31 and 33-39 if those claims are found allowable. However, it is respectfully suggested that this rejection overlooks some distinct differences between claims 9 and 31. Claim 31 recites patterning the crystalline semiconductor film to form at least one crystalline semiconductor island. In contrast, claim 9 does not recite patterning nor an island of this type. Therefore, there is in fact a difference in scope between these claims, and it is respectfully suggested that these claims are therefore not substantial duplicates and the provisional rejection should be withdrawn.

Claims 3-8, 18, 20-21 and 24-71 stand rejected under 35 USC 102(b) as allegedly being anticipated by applicant's specification. Apparently this is a rejection based on admitted

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prior art. In order to obviate this rejection, claims 6, 9, 31, 40, 55 and 64 have been amended to clarify the claimed invention. The amendments recite the first metal element added region being "away from" the second metal element added region. It is respectfully suggested that this is an important difference, and is not taught or suggested by the admitted prior art.

Claims 24-30 and 48-54 recite that the metal element added region has a length that extends 100 μm or more longer from an end region of the crystalline semiconductor island, in a longitudinal direction of the metal element added region. It is respectfully suggested that this is not taught in the description of the related art nor is this feature in any way admitted as prior art. Moreover, when the length is set to 50% or more of the crystal growth distance, the region where the semiconductor island region is formed can be set to a region where the crystal growth linearly progresses. See for example page 7 lines 7-9. The typical crystal growth distance is 100 μm or more see page 16 lines 2-4. 100 μm or more is long enough to obtain such a variable result. Figure 8 simply shows that the metal element added region 811 and 812 has a length extending longer from an end portion of the crystalline semiconductor island 801 and teaches nothing about this cited importance.

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Therefore, it is respectfully suggested that these claims are not properly rejected based on the admitted prior art.


The undersigned as also corrected the spelling error of the word inverter.

In view of the above amendments and remarks therefore, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

Please apply the \$110.00 one month extension fee and any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 05/29/03



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